

描述 / Descriptions

TO-220 塑封封装 N 沟道场效应管。

N-CHANNEL MOSFET in a TO-220 Plastic Package.

特征 / Features

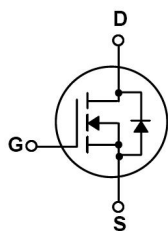
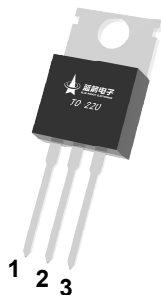
低电阻,开关速度快。

Ultra Low On-Resistance,fast switching.

用途 / Applications

该器件适用于高效电源模块, 主动式 PFC 电路和基于半桥拓扑结构的电子节能灯。

These devices are well suited for high efficient switched mode power supplies, Active power factor correction, electronic lamp ballast based on half bridge topology.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1 : G

PIN 2、4 : D

PIN 3 : S

印章代码 / Marking

见印章说明。 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V _{DSS}	100	V
Drain Current		I _D (Tc=25℃)	70	A
Pulsed Drain Current		I _{DM}	180	A
Gate-Source Voltage		V _{GS}	±20	V
Single Pulsed Avalanche Energy L=0.5mH		E _{AS}	78.8	mJ
Avalanche Current		I _{AS}	15	A
Total Power Dissipation		P _D (Tc=25℃)	107	W
Junction and Storage Temperature Range		T _J ,T _{STG}	-55 to 150	℃
Thermal Resistance-Junction to Ambient	t ≤ 10s	R _{θJA}	15	℃/W
	Steady-State		60	
Thermal Resistance-Junction to Case	Steady-State	R _{θJC}	1.4	

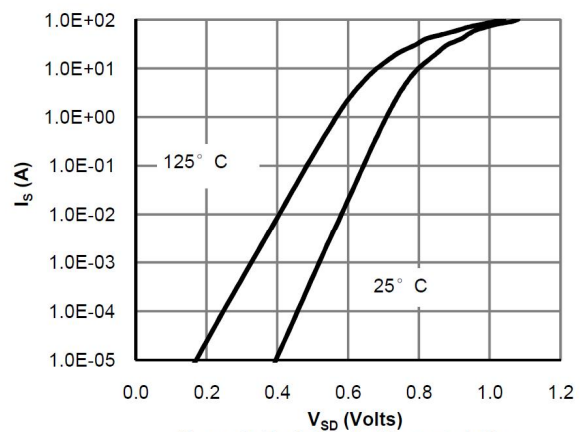
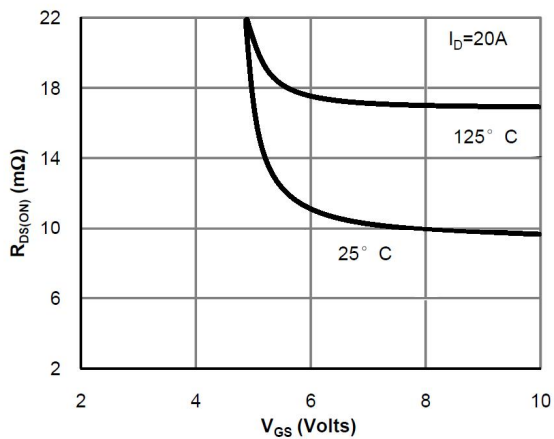
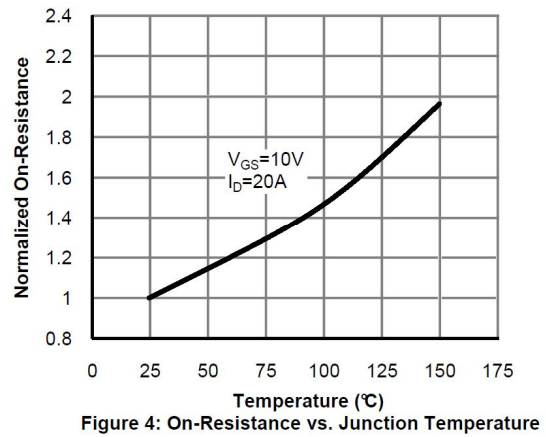
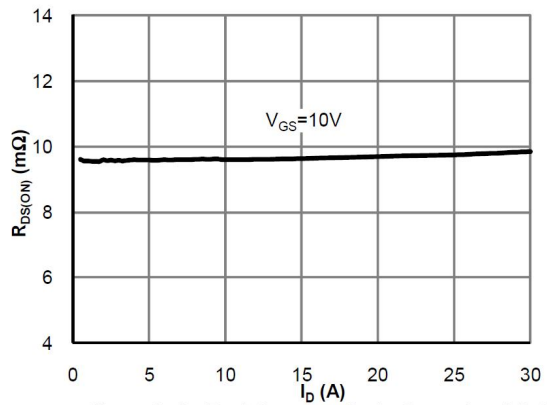
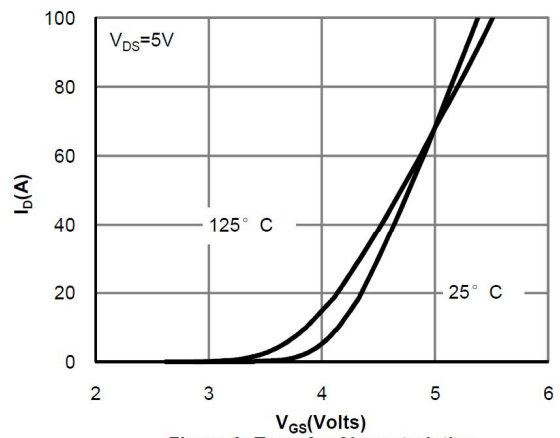
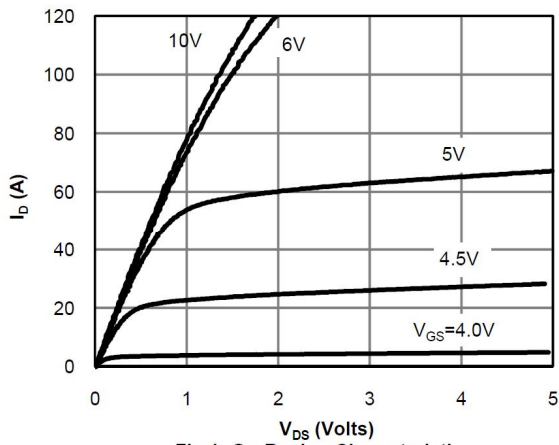
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	100	109		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V$ $V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2	3	4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		9.5	12	m Ω
Forward On Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.25	V
Gate resistance	R_g	$f=1\text{MHz}$		2		Ω
Input Capacitance	C_{iss}	$V_{DS}=25V$ $f=1\text{MHz}$ $V_{GS}=0V$		1830		pF
Output Capacitance	C_{oss}			900		
Reverse Transfer Capacitance	C_{rss}			105		

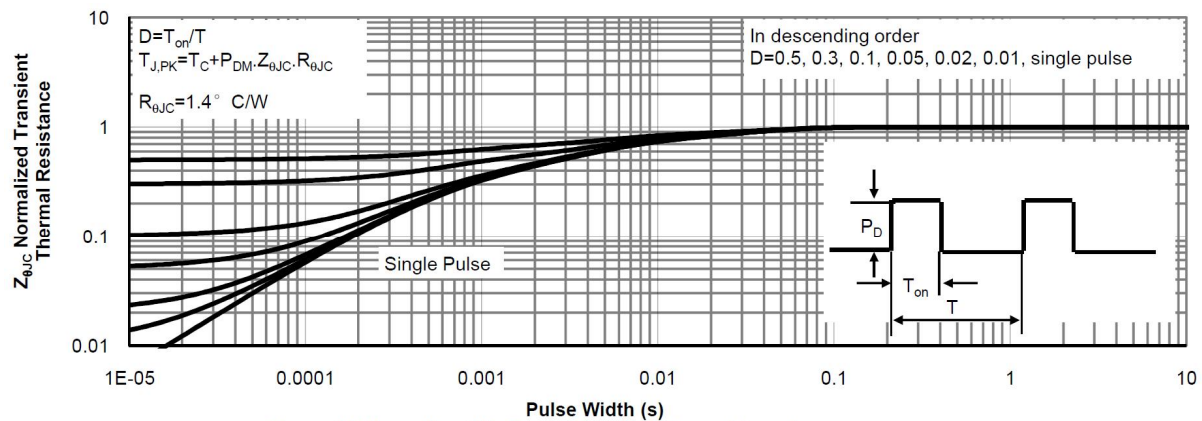
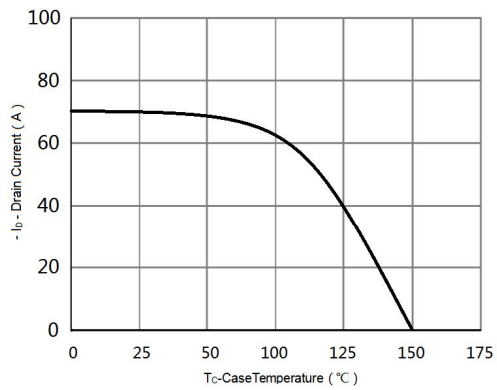
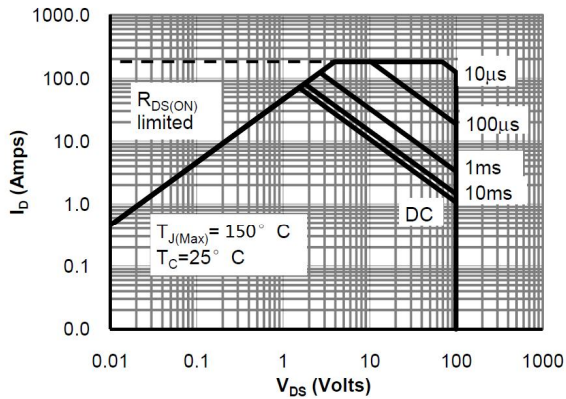
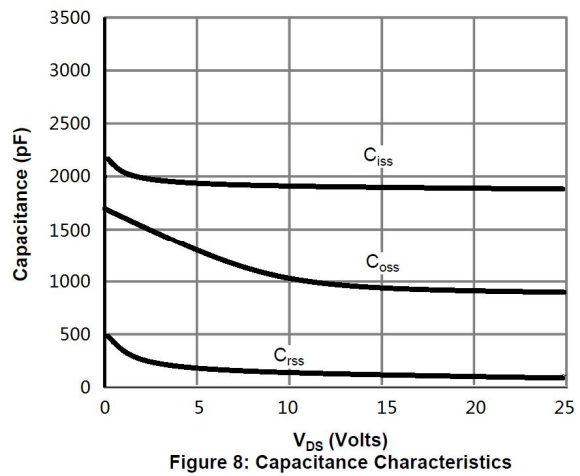
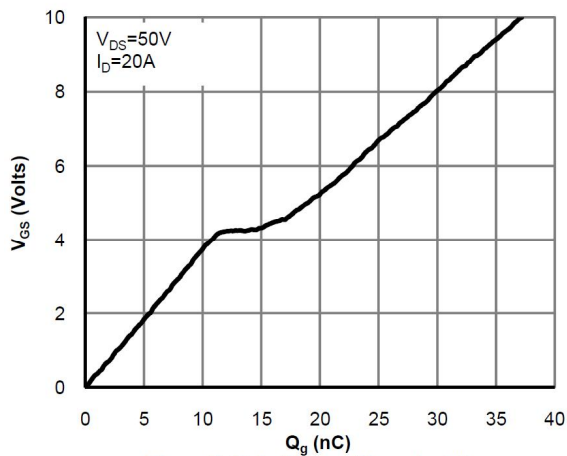
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Total Gate Charge	$Q_g(10V)$	$V_{GS}=10V$ $V_{DS}=50V$ $I_D=20A$		37		nC
Gate Source Charge	Q_{gs}			11.5		
Gate Drain Charge	Q_{gd}			5		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=50V$ $R_L=2.5\Omega$ $R_{GEN}=3\Omega$		13		ns
Turn-On Rise Time	t_r			8.5		
Turn-Off Delay Time	$t_{d(off)}$			29		
Turn-Off Fall Time	t_f			4		

电参数曲线图 / Electrical Characteristic Curve



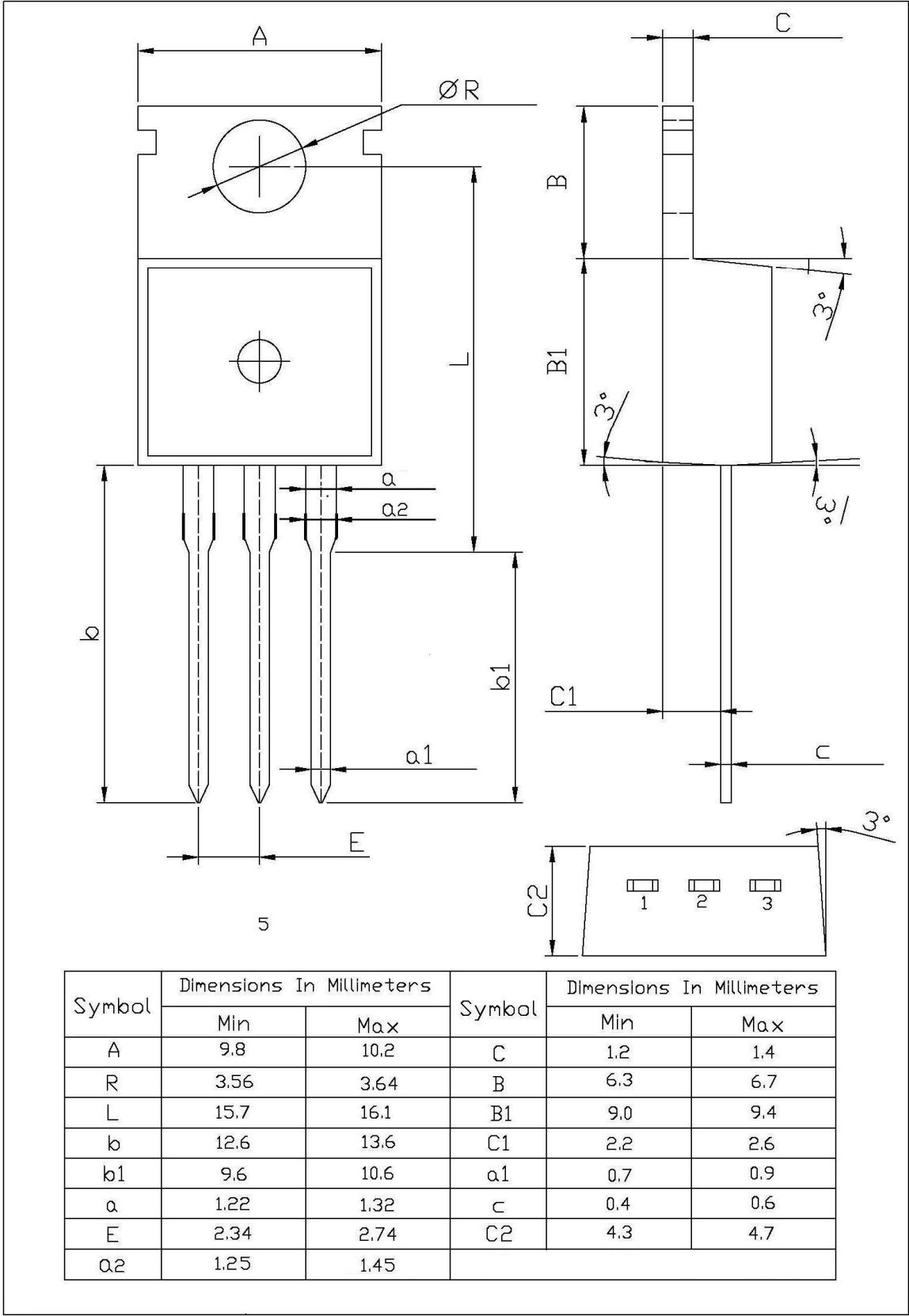
电参数曲线图 / Electrical Characteristic Curve



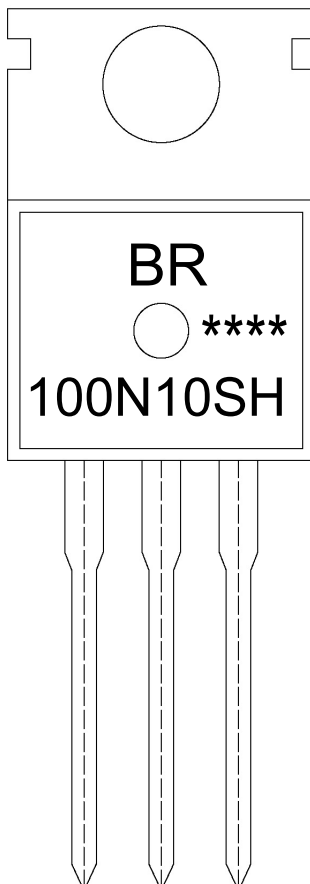
外形尺寸图 / Package Dimensions

T□-220

单位：mm



印章说明 / Marking Instructions



说明：

BR： 为公司代码

100N10SH： 为型号代码

****： 为生产批号代码，随生产批号变化

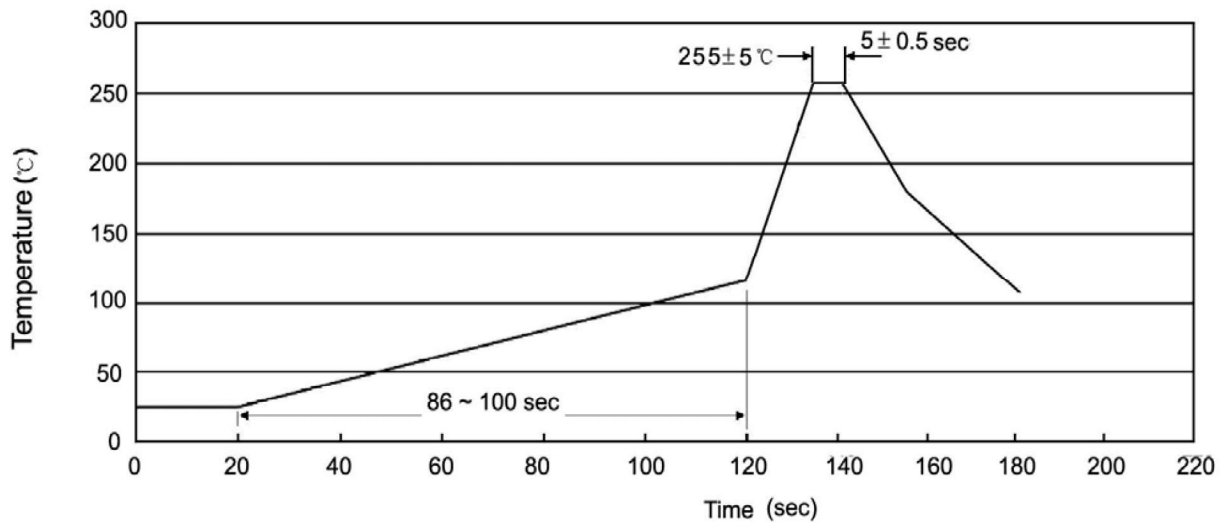
Note:

BR: Company Code

100N10SH: Product Type

****: Lot No. Code, code change with Lot No

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

1. 预热温度 25 ~ 150°C，时间 60 ~ 90sec;
2. 峰值温度 255±5°C，时间持续为 5±0.5sec;
3. 焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

1. Preheating: 25~150°C, Time: 60~90sec.
2. Peak Temp.: 255±5°C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.: 270±5°C

Time: 10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices